Jeffrey Bokor

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

 178
 10,496
 49
 99

 papers
 citations
 h-index
 g-index

 200
 12,220
 7.4
 5.86

 ext. papers
 ext. citations
 avg, IF
 L-index

#	Paper	IF	Citations
178	Magnetic state switching in FeGa microstructures. Smart Materials and Structures, 2022, 31, 035005	3.4	O
177	Progress toward picosecond on-chip magnetic memory. <i>Applied Physics Letters</i> , 2022 , 120, 140501	3.4	2
176	Bottom-Up Synthesized Nanoporous Graphene Transistors (Adv. Funct. Mater. 47/2021). <i>Advanced Functional Materials</i> , 2021 , 31, 2170348	15.6	1
175	Unifying femtosecond and picosecond single-pulse magnetic switching in Gd-Fe-Co. <i>Physical Review B</i> , 2021 , 103,	3.3	8
174	Synergetic Bottom-Up Synthesis of Graphene Nanoribbons by Matrix-Assisted Direct Transfer. Journal of the American Chemical Society, 2021 , 143, 4174-4178	16.4	4
173	Single-Domain Multiferroic Array-Addressable Terfenol-D (SMArT) Micromagnets for Programmable Single-Cell Capture and Release. <i>Advanced Materials</i> , 2021 , 33, e2006651	24	4
172	Engineering new limits to magnetostriction through metastability in iron-gallium alloys. <i>Nature Communications</i> , 2021 , 12, 2757	17.4	2
171	Localized strain profile in surface electrode array for programmable composite multiferroic devices. <i>Applied Physics Letters</i> , 2021 , 118, 182901	3.4	3
170	Single-Cell Manipulation: Single-Domain Multiferroic Array-Addressable Terfenol-D (SMArT) Micromagnets for Programmable Single-Cell Capture and Release (Adv. Mater. 20/2021). <i>Advanced Materials</i> , 2021 , 33, 2170159	24	1
169	Ultralow contact resistance between semimetal and monolayer semiconductors. <i>Nature</i> , 2021 , 593, 211	1-32:1.74	154
168	Local negative permittivity and topological phase transition in polar skyrmions. <i>Nature Materials</i> , 2021 , 20, 194-201	27	33
167	Role of element-specific damping in ultrafast, helicity-independent, all-optical switching dynamics in amorphous (Gd,Tb)Co thin films. <i>Physical Review B</i> , 2021 , 103,	3.3	14
166	Influence of dislocations and twin walls in BaTiO3 on the voltage-controlled switching of perpendicular magnetization. <i>Physical Review Materials</i> , 2021 , 5,	3.2	1
165	Bottom-Up Synthesized Nanoporous Graphene Transistors. <i>Advanced Functional Materials</i> , 2021 , 31, 2103798	15.6	1
164	Transfer-Free Synthesis of Atomically Precise Graphene Nanoribbons on Insulating Substrates. <i>ACS Nano</i> , 2021 , 15, 2635-2642	16.7	4
163	Statistically meaningful measure of domain-wall roughness in magnetic thin films. <i>Physical Review B</i> , 2020 , 101,	3.3	8
162	Manipulating magnetoelectric energy landscape in multiferroics. <i>Nature Communications</i> , 2020 , 11, 283	8617.4	18

(2018-2020)

161	Tunable Magnetoelastic Effects in Voltage-Controlled Exchange-Coupled Composite Multiferroic Microstructures. <i>ACS Applied Materials & Samp; Interfaces</i> , 2020 , 12, 6752-6760	9.5	10
160	Progress towards ultrafast spintronics applications. <i>Journal of Magnetism and Magnetic Materials</i> , 2020 , 502, 166478	2.8	24
159	Disk-shaped magnetic particles for cancer therapy. <i>Applied Physics Reviews</i> , 2020 , 7, 011306	17.3	10
158	A Dual Magnetic Tunnel Junction-Based Neuromorphic Device. <i>Advanced Intelligent Systems</i> , 2020 , 2, 2000143	6	4
157	Toward Intrinsic Ferroelectric Switching in Multiferroic BiFeO_{3}. <i>Physical Review Letters</i> , 2020 , 125, 067601	7.4	18
156	SpinBrbit torque switching of a ferromagnet with picosecond electrical pulses. <i>Nature Electronics</i> , 2020 , 3, 680-686	28.4	20
155	Nanomagnetic Particle-Based Information Processing. IEEE Nanotechnology Magazine, 2019, 18, 983-98	3 8 2.6	1
154	Low-Temperature Side Contact to Carbon Nanotube Transistors: Resistance Distributions Down to 10 nm Contact Length. <i>Nano Letters</i> , 2019 , 19, 1083-1089	11.5	21
153	Demonstration of spin transfer torque (STT) magnetic recording. <i>Applied Physics Letters</i> , 2019 , 114, 243	31504	1
152	Effects of Interface Induced Natural Strains on Magnetic Properties of FeRh. <i>Nanomaterials</i> , 2019 , 9,	5.4	5
151	Ultrafast magnetization switching in nanoscale magnetic dots. <i>Applied Physics Letters</i> , 2019 , 114, 23240	073.4	18
150	Intrinsic Controllable Magnetism of Graphene Grown on Fe. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 26870-26876	3.8	4
149	Electric-field controlled magnetic reorientation in exchange coupled CoFeB/Ni bilayer microstructures. <i>Journal of Physics: Conference Series</i> , 2019 , 1407, 012024	0.3	1
148	Influence of Nonuniform Micron-Scale Strain Distributions on the Electrical Reorientation of Magnetic Microstructures in a Composite Multiferroic Heterostructure. <i>Nano Letters</i> , 2018 , 18, 1952-19	96 ¹ 1 ^{1.5}	36
147	Bi-directional coupling in strain-mediated multiferroic heterostructures with magnetic domains and domain wall motion. <i>Scientific Reports</i> , 2018 , 8, 5207	4.9	25
146	Negative Differential Resistance and Steep Switching in Chevron Graphene Nanoribbon Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2018 , 39, 143-146	4.4	15
145	Enhanced magnetoelectric coupling in a composite multiferroic system via interposing a thin film polymer. <i>AIP Advances</i> , 2018 , 8, 055907	1.5	13
144	3D multilevel spin transfer torque devices. <i>Applied Physics Letters</i> , 2018 , 112, 112402	3.4	12

143	Self-assembled single-digit nanometer memory cells. <i>Applied Physics Letters</i> , 2018 , 113, 062404	3.4	2
142	Electrically controlled switching of the magnetization state in multiferroic BaTiO3/CoFe submicrometer structures. <i>Physical Review Materials</i> , 2018 , 2,	3.2	7
141	Cytocompatible magnetostrictive microstructures for nano- and microparticle manipulation on linear strain response piezoelectrics. <i>Multifunctional Materials</i> , 2018 , 1, 014004	5.2	5
140	Deterministic multi-step rotation of magnetic single-domain state in Nickel nanodisks using multiferroic magnetoelastic coupling. <i>Journal of Magnetism and Magnetic Materials</i> , 2017 , 439, 196-202	2.8	14
139	Interface Engineering of Domain Structures in BiFeO Thin Films. <i>Nano Letters</i> , 2017 , 17, 486-493	11.5	52
138	Short-channel field-effect transistors with 9-atom and 13-atom wide graphene nanoribbons. <i>Nature Communications</i> , 2017 , 8, 633	17.4	215
137	Single shot ultrafast all optical magnetization switching of ferromagnetic Co/Pt multilayers. <i>Applied Physics Letters</i> , 2017 , 111, 042401	3.4	43
136	Ultrafast magnetization reversal by picosecond electrical pulses. <i>Science Advances</i> , 2017 , 3, e1603117	14.3	77
135	Electric current induced ultrafast demagnetization. <i>Physical Review B</i> , 2017 , 96,	3.3	19
134	Ultrafast magnetic switching of GdFeCo with electronic heat currents. <i>Physical Review B</i> , 2017 , 95,	3.3	34
133	Model for multishot all-thermal all-optical switching in ferromagnets. <i>Physical Review B</i> , 2016 , 94,	3.3	46
132	Role of electron and phonon temperatures in the helicity-independent all-optical switching of GdFeCo. <i>Physical Review B</i> , 2016 , 94,	3.3	43
131	The Physics of Spin-Transfer Torque Switching in Magnetic Tunneling Junctions in Sub-10 nm Size Range. <i>IEEE Transactions on Magnetics</i> , 2016 , 52, 1-4	2	9
130	Design Requirements for a Spintronic MTJ Logic Device for Pipelined Logic Applications. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1754-1761	2.9	3
129	Experimental test of Landauer's principle in single-bit operations on nanomagnetic memory bits. <i>Science Advances</i> , 2016 , 2, e1501492	14.3	85
128	MoS2 transistors with 1-nanometer gate lengths. <i>Science</i> , 2016 , 354, 99-102	33.3	812
127	Switching of perpendicularly polarized nanomagnets with spin orbit torque without an external magnetic field by engineering a tilted anisotropy. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2015 , 112, 10310-5	11.5	162
126	Highly uniform carbon nanotube nanomesh network transistors. <i>Nano Research</i> , 2015 , 8, 1320-1326	10	11

(2012-2015)

125	Electrically driven magnetic domain wall rotation in multiferroic heterostructures to manipulate suspended on-chip magnetic particles. <i>ACS Nano</i> , 2015 , 9, 4814-26	16.7	69	
124	Sub-nanosecond signal propagation in anisotropy-engineered nanomagnetic logic chains. <i>Nature Communications</i> , 2015 , 6, 6466	17.4	22	
123	Deterministic Domain Wall Motion Orthogonal To Current Flow Due To Spin Orbit Torque. <i>Scientific Reports</i> , 2015 , 5, 11823	4.9	49	
122	Direct optical detection of current induced spin accumulation in metals by magnetization-induced second harmonic generation. <i>Applied Physics Letters</i> , 2015 , 107, 152404	3.4	7	
121	Deterministic doping and the exploration of spin qubits 2015 ,		7	
120	Time-Resolved Photo-Emission Electron Microscopy of Nanomagnetic Logic Chains. <i>Springer Proceedings in Physics</i> , 2015 , 281-283	0.2		
119	Stark shift and field ionization of arsenic donors in 28Si-silicon-on-insulator structures. <i>Applied Physics Letters</i> , 2014 , 104, 193502	3.4	15	
118	High-performance thin-film transistors produced from highly separated solution-processed carbon nanotubes. <i>Applied Physics Letters</i> , 2014 , 104, 143508	3.4	17	
117	Concave nanomagnets: investigation of anisotropy properties and applications to nanomagnetic logic. <i>Applied Physics A: Materials Science and Processing</i> , 2013 , 111, 413-421	2.6	13	
116	Bottom-up graphene nanoribbon field-effect transistors. <i>Applied Physics Letters</i> , 2013 , 103, 253114	3.4	178	
115	Short-channel transistors constructed with solution-processed carbon nanotubes. <i>ACS Nano</i> , 2013 , 7, 798-803	16.7	68	
114	Plasmonic near-field probes: a comparison of the campanile geometry with other sharp tips. <i>Optics Express</i> , 2013 , 21, 8166-76	3.3	50	
113	All-electrical nuclear spin polarization of donors in silicon. <i>Physical Review Letters</i> , 2013 , 110, 057601	7.4	10	
112	Nanofocusing in a metal i hsulator i hetal gap plasmon waveguide with a three-dimensional linear taper. <i>Nature Photonics</i> , 2012 , 6, 838-844	33.9	252	
111	Investigation of Defects and Errors in Nanomagnetic Logic Circuits. <i>IEEE Nanotechnology Magazine</i> , 2012 , 11, 760-762	2.6	39	
110	Streptavidin as CNTs and DNA Linker for the Specific Electronic and Optical Detection of DNA Hybridization. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 22579-22586	3.8	14	
109	Mapping local charge recombination heterogeneity by multidimensional nanospectroscopic imaging. <i>Science</i> , 2012 , 338, 1317-21	33.3	128	
108	Error immunity techniques for nanomagnetic logic 2012 ,		1	

107	Harnessing Chemical Raman Enhancement for Understanding Organic Adsorbate Binding on Metal Surfaces. <i>Journal of Physical Chemistry Letters</i> , 2012 , 3, 1357-62	6.4	23
106	Cascade-like signal propagation in chains of concave nanomagnets. <i>Applied Physics Letters</i> , 2012 , 100, 152406	3.4	19
105	Electrical activation and electron spin resonance measurements of implanted bismuth in isotopically enriched silicon-28. <i>Applied Physics Letters</i> , 2012 , 100, 172104	3.4	41
104	Comparative study of solution-processed carbon nanotube network transistors. <i>Applied Physics Letters</i> , 2012 , 101, 112104	3.4	23
103	Improved single ion implantation with scanning probe alignment. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 06FD04	1.3	11
102	Signal propagation in dipole coupled nanomagnets for logic applications 2012,		2
101	Electrically detected magnetic resonance in a W-band microwave cavity. <i>Review of Scientific Instruments</i> , 2011 , 82, 034704	1.7	6
100	Computing in Thermal Equilibrium With Dipole-Coupled Nanomagnets. <i>IEEE Nanotechnology Magazine</i> , 2011 , 10, 1401-1404	2.6	9
99	Radiation engineering of optical antennas for maximum field enhancement. <i>Nano Letters</i> , 2011 , 11, 26	06-1.9	129
98	Exploring the thermodynamic limits of computation in integrated systems: magnetic memory, nanomagnetic logic, and the Landauer limit. <i>Physical Review Letters</i> , 2011 , 107, 010604	7.4	76
97	Direct observation of imprinted antiferromagnetic vortex states in CoO/Fe/Ag(001) discs. <i>Nature Physics</i> , 2011 , 7, 303-306	16.2	66
96	Hyperspectral nanoscale imaging on dielectric substrates with coaxial optical antenna scan probes. <i>Nano Letters</i> , 2011 , 11, 1201-7	11.5	104
95	Ultimate device scaling: Intrinsic performance comparisons of carbon-based, InGaAs, and Si field-effect transistors for 5 nm gate length 2011 ,		58
94	Chemical Raman enhancement of organic adsorbates on metal surfaces. <i>Physical Review Letters</i> , 2011 , 106, 083003	7.4	109
93	Electrically detected magnetic resonance of neutral donors interacting with a two-dimensional electron gas. <i>Physical Review Letters</i> , 2011 , 106, 207601	7.4	22
92	Detecting single nanomagnet dynamics beyond the diffraction limit in varying magnetostatic environments. <i>Applied Physics Letters</i> , 2011 , 98, 052502	3.4	17
91	Electronic anabolic steroid recognition with carbon nanotube field-effect transistors. <i>ACS Nano</i> , 2010 , 4, 1473-80	16.7	16
90	Formation of bandgap and subbands in graphene nanomeshes with sub-10 nm ribbon width fabricated via nanoimprint lithography. <i>Nano Letters</i> , 2010 , 10, 2454-60	11.5	267

(2007-2010)

89	Direct chemical vapor deposition of graphene on dielectric surfaces. <i>Nano Letters</i> , 2010 , 10, 1542-8	11.5	387
88	Characterization of the junction capacitance of metal-semiconductor carbon nanotube Schottky contacts. <i>Applied Physics Letters</i> , 2010 , 96, 013103	3.4	17
87	Gold nanoparticle self-similar chain structure organized by DNA origami. <i>Journal of the American Chemical Society</i> , 2010 , 132, 3248-9	16.4	457
86	Spin-dependent scattering in a silicon transistor. <i>Physical Review B</i> , 2009 , 80,	3.3	13
85	Device fabrication and transport measurements of FinFETs built with28Si SOI wafers toward donor qubits in silicon. <i>Semiconductor Science and Technology</i> , 2009 , 24, 105022	1.8	7
84	Dopant profiling and surface analysis of silicon nanowires using capacitance-voltage measurements. <i>Nature Nanotechnology</i> , 2009 , 4, 311-4	28.7	145
83	Mapping of ion beam induced current changes in FinFETs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2009 , 267, 1222-1225	1.2	8
82	Critical issues in the formation of quantum computer test structures by ion implantation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2009 , 267, 2563-2566	1.2	16
81	DNA directed assembly of nanoparticle linear structure for nanophotonics. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 184		6
80	Label-free DNA biosensors based on functionalized carbon nanotube field effect transistors. <i>Nano Letters</i> , 2009 , 9, 530-6	11.5	145
79	Diameter-dependent electron mobility of InAs nanowires. <i>Nano Letters</i> , 2009 , 9, 360-5	11.5	328
78	Simulation studies of nanomagnet-based logic architecture. <i>Nano Letters</i> , 2008 , 8, 4173-8	11.5	137
77	Single atom doping for quantum device development in diamond and silicon. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 2596-2600		39
76	Mechanical detection and mode shape imaging of vibrational modes of micro and nanomechanical resonators by dynamic force microscopy. <i>Journal of Physics: Conference Series</i> , 2008 , 100, 052009	0.3	2
75	Mode shape imaging of out-of-plane and in-plane vibrating RF micromechanical resonators by atomic force microscopy. <i>Microelectronic Engineering</i> , 2007 , 84, 1354-1357	2.5	8
74	Spin-dependent scattering off neutral antimony donors in Si28 field-effect transistors. <i>Applied Physics Letters</i> , 2007 , 91, 242106	3.4	34
73	Optimization of nano-magneto-optic sensitivity using dual dielectric layer enhancement. <i>Applied Physics Letters</i> , 2007 , 90, 252504	3.4	17
72	Detection of nanomechanical vibrations by dynamic force microscopy in higher cantilever eigenmodes. <i>Applied Physics Letters</i> , 2007 , 91, 053116	3.4	18

71	Detection of low energy single ion impacts in micron scale transistors at room temperature. <i>Applied Physics Letters</i> , 2007 , 91, 193502	3.4	26
70	Size dependent damping in picosecond dynamics of single nanomagnets. <i>Applied Physics Letters</i> , 2007 , 90, 202504	3.4	51
69	Electrical activation and electron spin coherence of ultralow dose antimony implants in silicon. <i>Applied Physics Letters</i> , 2006 , 88, 112101	3.4	64
68	Magneto-optical observation of picosecond dynamics of single nanomagnets. <i>Nano Letters</i> , 2006 , 6, 293	39 -44	83
67	Effect of diameter variation in a large set of carbon nanotube transistors. <i>Nano Letters</i> , 2006 , 6, 1364-8	11.5	52
66	Strategies for integration of donor electron spin qubits in silicon. <i>Microelectronic Engineering</i> , 2006 , 83, 1814-1817	2.5	9
65	Cavity-enhanced magnetooptical observation of magnetization reversal in individual single-domain nanomagnets. <i>Nano Letters</i> , 2005 , 5, 1413-7	11.5	34
64	A comparison study of symmetric ultrathin-body double-gate devices with metal source/drain and doped source/drain. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 1859-1867	2.9	82
63	Structural optimization of SUTBDG devices for low-power applications. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 360-366	2.9	5
62	Ion implantation with scanning probe alignment. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 2798		13
61	Scanning acoustic force microscopy characterization of thermal expansion effects on the electromechanical properties of film bulk acoustic resonators. <i>Applied Physics Letters</i> , 2005 , 86, 084102	3.4	5
60	Mechanical elasticity of single and double clamped silicon nanobeams fabricated by the vapor-liquid-solid method. <i>Applied Physics Letters</i> , 2005 , 87, 053111	3.4	109
59	Single ion implantation with scanning probe alignment. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 2992		10
58	Characterization of the ultrathin vertical channel CMOS technology. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 106-112	2.9	8
57	A simulation study of gate line edge roughness effects on doping profiles of short-channel MOSFET devices. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 228-232	2.9	43
56	Sensitive detection of laser damage to Mo/Si multilayers by picosecond ultrasonics. <i>Applied Physics B: Lasers and Optics</i> , 2004 , 79, 107-112	1.9	3
55	Is gate line edge roughness a first-order issue in affecting the performance of deep sub-micro bulk MOSFET devices?. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2004 , 17, 357-361	2.6	29
54	Monolithic Integration of Carbon Nanotube Devices with Silicon MOS Technology. <i>Nano Letters</i> , 2004 , 4, 123-127	11.5	105

(1999-2003)

53	Sensitivity of double-gate and FinFETDevices to process variations. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 2255-2261	2.9	143
52	Fabrication of Sub-10-nm Silicon Nanowire Arrays by Size Reduction Lithography. <i>Journal of Physical Chemistry B</i> , 2003 , 107, 3340-3343	3.4	153
51	Solid state quantum computer development in silicon with single ion implantation. <i>Journal of Applied Physics</i> , 2003 , 94, 7017-7024	2.5	83
50	Hydrogen annealing effect on DC and low-frequency noise characteristics in CMOS FinFETs. <i>IEEE Electron Device Letters</i> , 2003 , 24, 186-188	4.4	40
49	Investigation of NiSi and TiSi as CMOS gate materials. <i>IEEE Electron Device Letters</i> , 2003 , 24, 634-636	4.4	40
48	. Proceedings of the IEEE, 2003 , 9, 1860-1873	14.3	157
47	Low-frequency noise characteristics of ultrathin body p-MOSFETs with molybdenum gate. <i>IEEE Electron Device Letters</i> , 2003 , 24, 31-33	4.4	9
46	Design and fabrication of 50-nm thin-body p-MOSFETs with a SiGe heterostructure channel. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 279-286	2.9	25
45	Low-frequency noise characteristics in p-channel FinFETs. IEEE Electron Device Letters, 2002, 23, 722-72	244.4	15
44	Gate line-edge roughness effects in 50-nm bulk MOSFET devices 2002 , 4689, 733		36
44	Gate line-edge roughness effects in 50-nm bulk MOSFET devices 2002 , 4689, 733 . <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 880-886	2.9	36 184
		2.9	
43	. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 880-886 Sub-60-nm quasi-planar FinFETs fabricated using a simplified process. <i>IEEE Electron Device Letters</i> ,		184
43	. IEEE Transactions on Electron Devices, 2001, 48, 880-886 Sub-60-nm quasi-planar FinFETs fabricated using a simplified process. IEEE Electron Device Letters, 2001, 22, 487-489 FinFET-a self-aligned double-gate MOSFET scalable to 20 nm. IEEE Transactions on Electron Devices,	4.4	184
43 42 41	. IEEE Transactions on Electron Devices, 2001, 48, 880-886 Sub-60-nm quasi-planar FinFETs fabricated using a simplified process. IEEE Electron Device Letters, 2001, 22, 487-489 FinFET-a self-aligned double-gate MOSFET scalable to 20 nm. IEEE Transactions on Electron Devices, 2000, 47, 2320-2325 Extreme ultraviolet carrier-frequency shearing interferometry of a lithographic four-mirror optical system. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society	4.4	184 99 1005
43 42 41 40	. IEEE Transactions on Electron Devices, 2001, 48, 880-886 Sub-60-nm quasi-planar FinFETs fabricated using a simplified process. IEEE Electron Device Letters, 2001, 22, 487-489 FinFET-a self-aligned double-gate MOSFET scalable to 20 nm. IEEE Transactions on Electron Devices, 2000, 47, 2320-2325 Extreme ultraviolet carrier-frequency shearing interferometry of a lithographic four-mirror optical system. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2939 Nanoscale ultra-thin-body silicon-on-insulator P-MOSFET with a SiGe/Si heterostructure channel.	2.9	184 99 1005 43
43 42 41 40 39	. IEEE Transactions on Electron Devices, 2001, 48, 880-886 Sub-60-nm quasi-planar FinFETs fabricated using a simplified process. IEEE Electron Device Letters, 2001, 22, 487-489 FinFET-a self-aligned double-gate MOSFET scalable to 20 nm. IEEE Transactions on Electron Devices, 2000, 47, 2320-2325 Extreme ultraviolet carrier-frequency shearing interferometry of a lithographic four-mirror optical system. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2939 Nanoscale ultra-thin-body silicon-on-insulator P-MOSFET with a SiGe/Si heterostructure channel. IEEE Electron Device Letters, 2000, 21, 161-163	2.9	184 99 1005 43 39

35	Thermal Stabilization of Non-Stoichiometric GaAs through Beryllium Doping. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 510, 55		
34	Minimum critical defects in extreme-ultraviolet lithography masks. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 2467		13
33	High field hole velocity and velocity overshoot in silicon inversion layers. <i>IEEE Electron Device Letters</i> , 1997 , 18, 54-56	4.4	17
32	AC output conductance of SOI MOSFETs and impact on analog applications. <i>IEEE Electron Device Letters</i> , 1997 , 18, 36-38	4.4	13
31	Dynamic threshold-voltage MOSFET (DTMOS) for ultra-low voltage VLSI. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 414-422	2.9	233
30	High-field transport of inversion-layer electrons and holes including velocity overshoot. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 664-671	2.9	20
29	High-intensity terahertz pulses at 1-kHz repetition rate. <i>IEEE Journal of Quantum Electronics</i> , 1996 , 32, 1839-1846	2	91
28	Noncontact probing of metal-oxide-semiconductor inversion layer mobility. <i>Applied Physics Letters</i> , 1996 , 69, 1779-1780	3.4	3
27	Surface adhesion reduction in silicon microstructures using femtosecond laser pulses. <i>Applied Physics Letters</i> , 1996 , 68, 197-199	3.4	28
26	Advanced lithography for ULSI. <i>IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems</i> , 1996 , 12, 11-15		2
25	Ultrafast carrier dynamics on the Si(100)2 x 1 surface. <i>Physical Review B</i> , 1996 , 54, R17300-R17303	3.3	25
24	ULTRAFAST HOT ELECTRON RELAXATION IN METALS. Advanced Series in Physical Chemistry, 1995 , 327	-346	1
23	Observation of the Thermalization of Electrons in a Metal Excited by Femtosecond Optical Pulses. <i>Springer Series in Chemical Physics</i> , 1993 , 331-334	0.3	
22	Direct measurement of nonequilibrium electron-energy distributions in subpicosecond laser-heated gold films. <i>Physical Review Letters</i> , 1992 , 68, 2834-2837	7.4	402
21	Electron thermalization in gold. <i>Physical Review B</i> , 1992 , 46, 13592-13595	3.3	397
20	Multiphoton ultraviolet spectroscopy of some 6p levels in krypton. <i>Physical Review A</i> , 1980 , 21, 1453-1	4 5 96	65
19	ArF laser photolysis of OCSe. II. Effect of vibrational excitation on Se(1S) quantum yields. <i>Journal of Chemical Physics</i> , 1979 , 70, 5593-5597	3.9	10
18	Doppler-free spectroscopy of the 2 band in 14NH3: Application to 16-fh generation. <i>Journal of Applied Physics</i> , 1979 , 50, 4541-4544	2.5	8

LIST OF PUBLICATIONS

17	Time-resolved reflectivity measurement of thermally stabilized low temperature grown GaAs doped with beryllium	1
16	Reliability study of CMOS FinFETs	5
15	FinFET process refinements for improved mobility and gate work function engineering	49
14	Complementary silicide source/drain thin-body MOSFETs for the 20 nm gate length regime	96
13	60 nm planarized ultra-thin body solid phase epitaxy MOSFETs	3
12	Gate length scaling and threshold voltage control of double-gate MOSFETs	57
11	30 nm ultra-thin-body SOI MOSFET with selectively deposited Ge raised S/D	10
10	FinFET-a quasi-planar double-gate MOSFET	12
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8	Quasi-planar NMOS FinFETs with sub-100 nm gate lengths	9
7	Remote charge scattering in MOSFETs with ultra-thin gate dielectrics	15
6	MOSFETs with 9 to 13 A thick gate oxides	12
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